

SFW



PATENT  
Customer No. 22,852  
Attorney Docket No. 04329.3247-00

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of:	)	
KATSUYUKI SEKINE ET AL.	)	
Application No.: 10/785,074	)	Group Art Unit: 2823
Filed: February 25, 2004	)	Examiner: W. M. Brewster
For: SEMICONDUCTOR DEVICE AND	)	Confirmation No.: 8935
MANUFACTURING METHOD	)	
THEREOF	)	

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**RESPONSE TO RESTRICTION REQUIREMENT**

In a restriction requirement mailed December 13, 2005, the period for response to which extends through January 13, 2006, the Examiner required restriction under 35 U.S.C. § 121 between Group I (claims 1-9), characterized by the Examiner as being drawn to means of controlling surface effects including three or more insulating layers; and Group II (claims 10-20), characterized by the Examiner as being drawn to silicon oxide formation with wave energy.

If Group I is elected, the Examiner further required Applicants to elect one of the following single species within Group 1: Species I (claims 1, 4, and 7), allegedly drawn to a maximal value of concentration of the helium in a surface portion on the semiconductor region side and a maximal value of concentration of the nitrogen in a surface portion on a side opposite to the semiconductor region; and Species II (claims

2, 3, 5, 6, 8 and 9), allegedly drawn to a maximal value of concentration of the nitrogen in a surface portion on the semiconductor region side and a second maximal value of concentration on the nitrogen in a surface portion on a side opposite to the semiconductor region.

If Group II is elected, the Examiner additionally required Applicants to elect one of the following species within Group II: Species I (claims 10, 11, 14, 17 and 19), allegedly drawn to heating a semiconductor region and silicon oxide film in a helium gas atmosphere, forming an insulating film including silicon, oxygen, and nitrogen; and Species II (claims 12, 13, 15, 16, 18 and 20), allegedly drawn to nitriding silicon oxide, changing a film forming condition at least once in the course of formation of the insulating film.


Applicants elect to prosecute Group II, Species I, and claims 10, 11, 14, 17 and 19, readable thereon, without traverse.

Please grant any extensions of time required to enter this response and charge any additional required fees to our deposit account 06-0916.

Respectfully submitted,

FINNEGAN, HENDERSON, FARABOW,  
GARRETT & DUNNER, L.L.P.

Dated: January 13, 2005

By:   
Steven L. Ashburn  
Reg. No. 56,636